

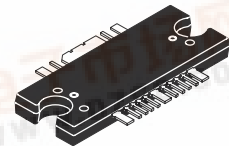
## The RF Line RF LDMOS Wideband Integrated Power Amplifiers

The MW4IC915MB/GMB wideband integrated circuit is designed for GSM and GSM EDGE base station applications. It uses Motorola's newest High Voltage (26 to 28 Volts) LDMOS IC technology and integrates a multi-stage structure. Its wideband On Chip design makes it usable from 750 to 1000 MHz. The linearity performances cover all modulations for cellular applications: GSM, GSM EDGE, TDMA, N-CDMA and W-CDMA.

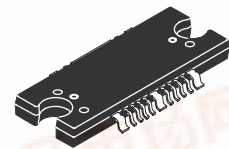
- Typical GSM/GSM EDGE Performances: 26 Volts,  $I_{DQ1} = 60 \text{ mA}$ ,  $I_{DQ2} = 240 \text{ mA}$ , 869-894 MHz and 921-960 MHz  
 Output Power — 3 Watts Avg.  
 Power Gain — 31 dB  
 Efficiency — 19%  
 Spectral Regrowth @ 400 kHz Offset = -65 dBc  
 Spectral Regrowth @ 600 kHz Offset = -83 dBc  
 EVM — 1.5%
- Typical Performance: 860-960 MHz, 26 Volts  
 Output Power — 15 Watts CW  
 Power Gain — 30 dB  
 Efficiency — 44%
- On Chip Matching (50 Ohm Input, >3 Ohm Output)
- Integrated Temperature Compensation Capability with Enable/Disable Function
- Integrated ESD Protection
- Capable of Handling 5:1 VSWR, @ 26 Vdc,  $f = 921 \text{ MHz}$ ,  
 $P_{out} = 15 \text{ W CW}$ ,  $I_{DQ1} = 90 \text{ mA}$ ,  $I_{DQ2} = 240 \text{ mA}$
- Can Be Bolted or Soldered through a Hole in the Circuit Board for Maximum Thermal Performance
- Also Available in Gull Wing for Surface Mount
- In Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.

### MW4IC915MBR1 MW4IC915GMBR1

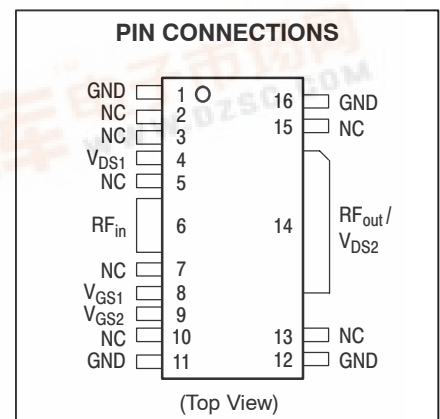
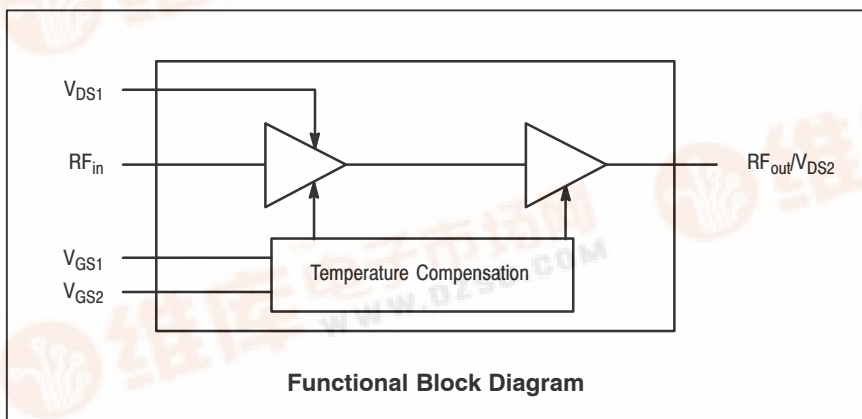
GSM/GSM EDGE,  
N-CDMA, W-CDMA  
860 - 960 MHz, 15 W, 26 V  
RF LDMOS WIDEBAND  
INTEGRATED POWER AMPLIFIERS



CASE 1329-09  
TO-272 WB-16  
PLASTIC  
MW4IC915MBR1



CASE 1329A-03  
TO-272 WB-16 GULL  
PLASTIC  
MW4IC915GMBR1



# Freescale Semiconductor, Inc.

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	65	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5. +15	Vdc
Storage Temperature Range	$T_{stg}$	-65 to +175	°C
Operating Junction Temperature	$T_J$	175	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
GSM Application ( $P_{out} = 15$ W CW) Stage 1, 26 Vdc, $I_{DQ} = 60$ mA Stage 2, 26 Vdc, $I_{DQ} = 240$ mA		1.48	
GSM EDGE Application ( $P_{out} = 7.5$ W CW) Stage 1, 26 Vdc, $I_{DQ} = 60$ mA Stage 2, 26 Vdc, $I_{DQ} = 240$ mA		1.59	
CDMA Application ( $P_{out} = 3.75$ W CW) Stage 1, 26 Vdc, $I_{DQ} = 60$ mA Stage 2, 26 Vdc, $I_{DQ} = 240$ mA		1.63	

## ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M3 (Minimum)
Charge Device Model	C2 (Minimum)

## MOISTURE SENSITIVITY LEVEL

Test Methodology	Rating
Per JESD 22-A113	3

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

### TWO-TONE FUNCTIONAL TESTS (In Motorola Test Fixture, 50 ohm system)

Two-Tone Common-Source Amplifier Power Gain ( $V_{DS} = 26$ Vdc, $P_{out} = 15$ W PEP, $I_{DQ1} = 90$ mA, $I_{DQ2} = 240$ mA, $f_1 = 869$ MHz, $f_2 = 869.1$ MHz and $f_1 = 960$ MHz and $f_2 =$ $960.1$ MHz)	$G_{ps}$	29	31	—	dB
Drain Efficiency ( $V_{DS} = 26$ Vdc, $P_{out} = 15$ W PEP, $I_{DQ1} = 90$ mA, $I_{DQ2} = 240$ mA, $f_1 = 869$ MHz, $f_2 = 869.1$ MHz and $f_1 = 960$ MHz and $f_2 =$ $960.1$ MHz)	$\eta$	29	31	—	%
Third Order Intermodulation Distortion ( $V_{DS} = 26$ Vdc, $P_{out} = 15$ W PEP, $I_{DQ1} = 90$ mA, $I_{DQ2} = 240$ mA, $f_1 = 869$ MHz, $f_2 = 869.1$ MHz and $f_1 = 960$ MHz and $f_2 =$ $960.1$ MHz)	IMD3	—	-40	-29	dBc
Input Return Loss ( $V_{DS} = 26$ Vdc, $P_{out} = 15$ W PEP, $I_{DQ1} = 90$ mA, $I_{DQ2} = 240$ mA, $f_1 = 869$ MHz, $f_2 = 869.1$ MHz and $f_1 = 960$ MHz and $f_2 =$ $960.1$ MHz)	IRL	—	-15	-10	dB

(continued)

# Freescale Semiconductor, Inc.

## ELECTRICAL CHARACTERISTICS - continued (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

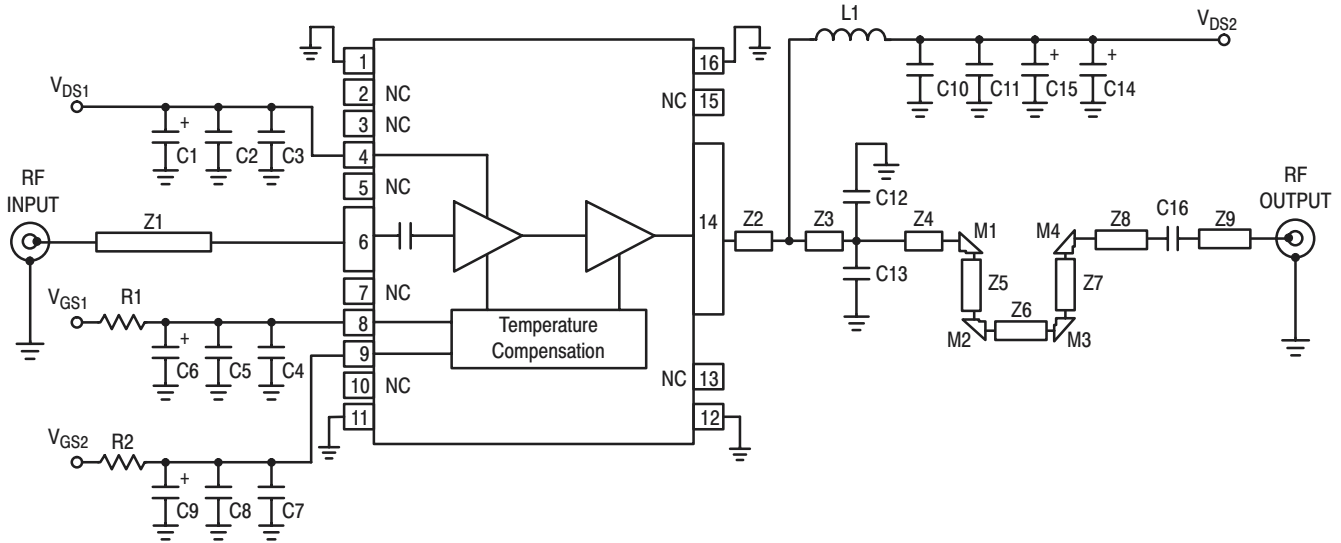
### PERFORMANCE TESTS (In Motorola Reference Board) V<sub>DS</sub> = 26 V, I<sub>DQ1</sub> = 60 mA, I<sub>DQ2</sub> = 240 mA

Quiescent Current Accuracy over Temperature (-10 to 85°C) at Nominal Value	ΔI <sub>QT</sub>	—	±5	—	%
Gain Flatness in 40 MHz Bandwidth @ P <sub>out</sub> = 3 W CW (Characterize from 869-894 MHz and 920-960 MHz)	G <sub>F</sub>	—	0.2	—	dB
Deviation from Linear Phase in 40 MHz Bandwidth @ P <sub>out</sub> = 3 W CW (Characterize from 869-894 MHz and 920-960 MHz)	Φ	—	±0.6	—	°
Delay @ P <sub>out</sub> = 3 W CW	Delay	—	2.5	—	ns
Insertion Phase Window @ P <sub>out</sub> = 3 W CW	ΦΔ	—	±15	—	°

### TYPICAL PERFORMANCE GSM/GSM EDGE (In Motorola Reference Board) V<sub>DS</sub> = 26 V, I<sub>DQ1</sub> = 60 mA, I<sub>DQ2</sub> = 240 mA, 869-894 MHz and 921-960 MHz

Output Power at 1dB Compression Point	P1dB	—	20	—	Watts
Common-Source Amplifier Power Gain (P <sub>out</sub> = 15 W CW)	G <sub>ps</sub>	—	30	—	dB
Drain Efficiency (P <sub>out</sub> = 15 W CW)	η	—	44	—	%
Input Return Loss (P <sub>out</sub> = 15 W CW)	IRL	—	-15	—	dB
Error Vector Magnitude (P <sub>out</sub> = 3 W Avg. including 0.6% rms source EVM)	EVM	—	1.5	—	%
Spectral Regrowth at 400 kHz Offset (P <sub>out</sub> = 3 W Avg.)	SR1	—	-65	—	dBc
Spectral Regrowth at 600 kHz Offset (P <sub>out</sub> = 3 W Avg.)	SR2	—	-83	—	dBc

## Freescale Semiconductor, Inc.



Z1	0.086" x 50 Ω Microstrip	Z6	0.157" x 0.283" Microstrip
Z2	0.133" x 0.236" Microstrip	Z7	0.429" x 0.283" Microstrip
Z3	0.435" x 0.283" Microstrip	Z8	0.394" x 0.088" Microstrip
Z4	0.171" x 0.283" Microstrip	Z9	0.181" x 0.088" Microstrip
Z5	0.429" x 0.283" Microstrip	PCB	Taconic TLX8, 0.030", ε <sub>r</sub> = 2.55

**Figure 1. Two-Tone 860-960 MHz Test Fixture Schematic**

**Table 1. Two-Tone 860-960 MHz Test Fixture Component Designations and Values**

Designators	Description
C1, C6, C9, C14	22 μF, 35 V Tantalum Chip Capacitors, AVX #TAJE226M035R
C2, C5, C8, C11	1000 pF Chip Capacitors, B Case, ATC #100B102JCA500X
C3, C4, C7, C10, C16	22 pF Chip Capacitors, B Case, ATC #100B220JCA500X
C12, C13	10 pF Chip Capacitors, B Case, ATC #100B100JCA500X
C15	10 μF Tantalum Chip Capacitor, Kemet #T491X226K035AS4394
R1, R2	10 kΩ, 1/4 W Chip Resistor (1206)
L1	12.5 nH Inductor
M1, M2, M3, M4	0.283", 90° Mitered Microstrip Bends

Freescale Semiconductor, Inc.

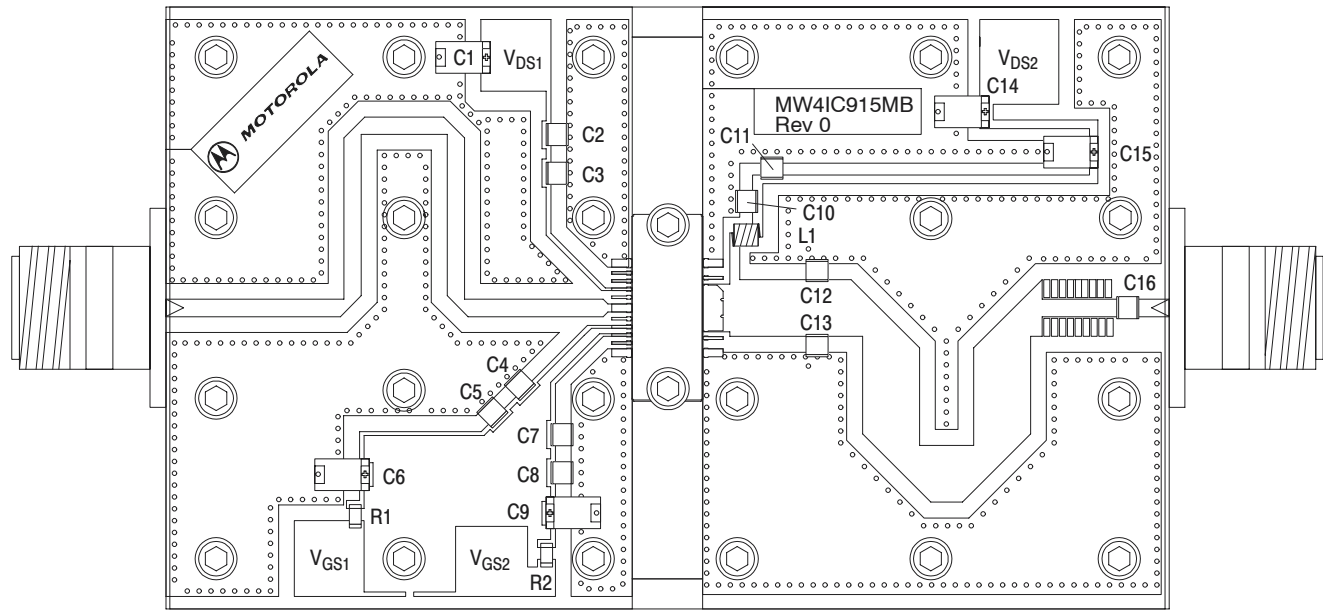
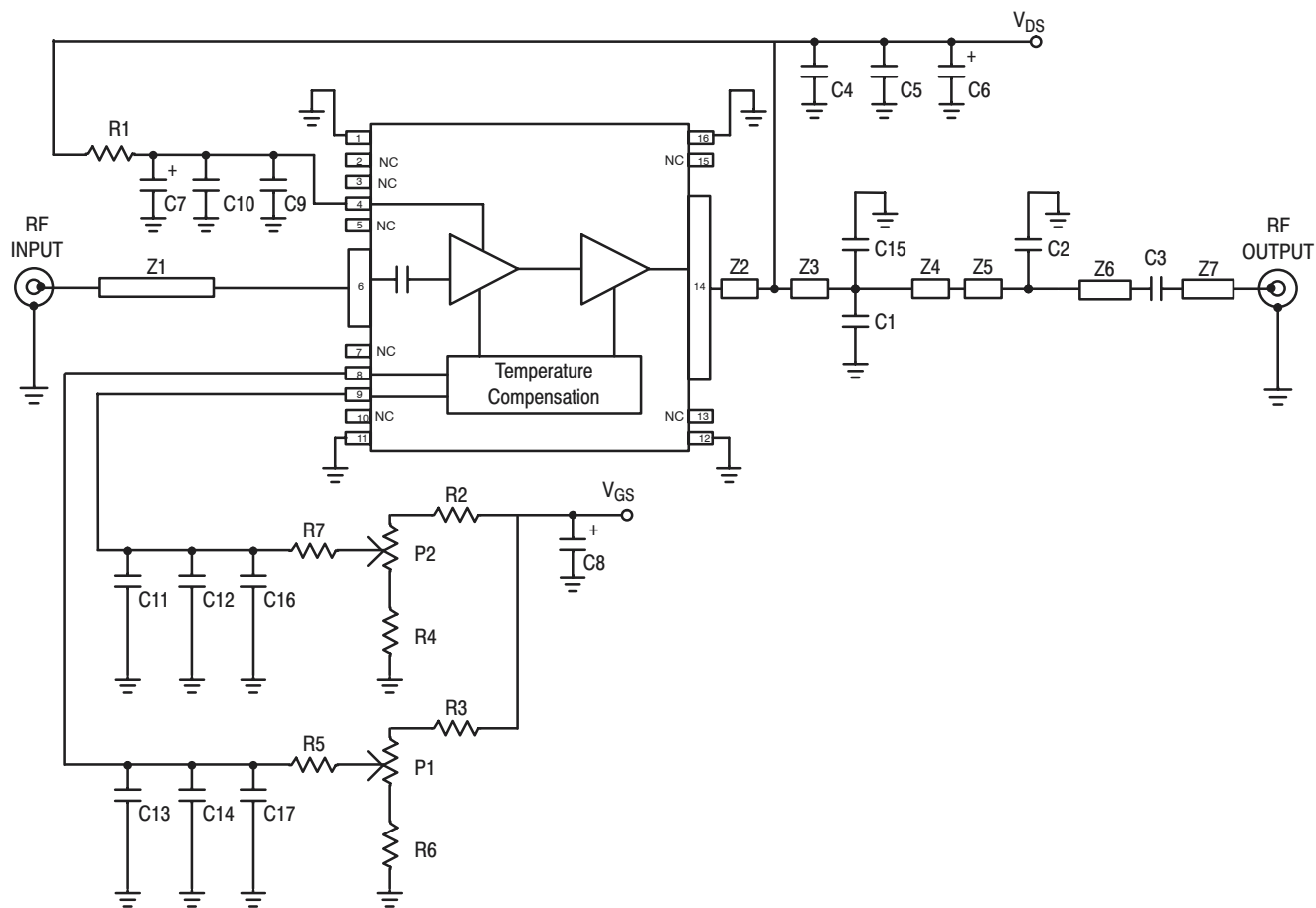


Figure 2. Two-Tone 860-960 MHz Test Fixture Component Layout

# Freescale Semiconductor, Inc.



Z1	0.681" x 0.039", 50 Ω Microstrip	Z5	0.566" x 0.043" Microstrip
Z2	0.157" x 0.228" Microstrip	Z6	0.165" x 0.043" Microstrip
Z3	0.468" x 0.157" Microstrip	Z7	0.078" x 0.043" Microstrip
Z4	0.220" x 0.157" Microstrip	PCB	Taconic RF35, 0.02", ε <sub>r</sub> = 3.5

Figure 3. 860-960 MHz Reference Board Schematic

Table 2. 860-960 MHz Reference Board Component Designations and Values

Designators	Description
C1, C15	10 pF Chip Capacitors (0805), ACCU-P AVX #08051J100GBT
C2	5.6 pF Chip Capacitor (0805), ACCU-P AVX #08051J5R6BBT
C3, C4, C9, C11, C13	33 pF Chip Capacitors (0805), ACCU-P AVX #08051J330GB
C5, C10, C12, C14	10 nF Chip Capacitors (0805), AVX #08055C103KAT
C6, C7, C8	22 μF, 35 V Tantalum Capacitors, AVX #TAJE226M035R
C16, C17	100 nF Chip Capacitors (0805), AVX #08055C104KAT
P1, P2	5 kΩ Potentiometer CMS Cermet Multi-turn, Bourns #3224W
R1, R2, R3, R4, R5	0 Ω, 1/8 W Chip Resistors (0805)
R6, R7	10 kΩ, 1/4 W Chip Resistors (1206)

Freescale Semiconductor, Inc.

# Freescale Semiconductor, Inc.

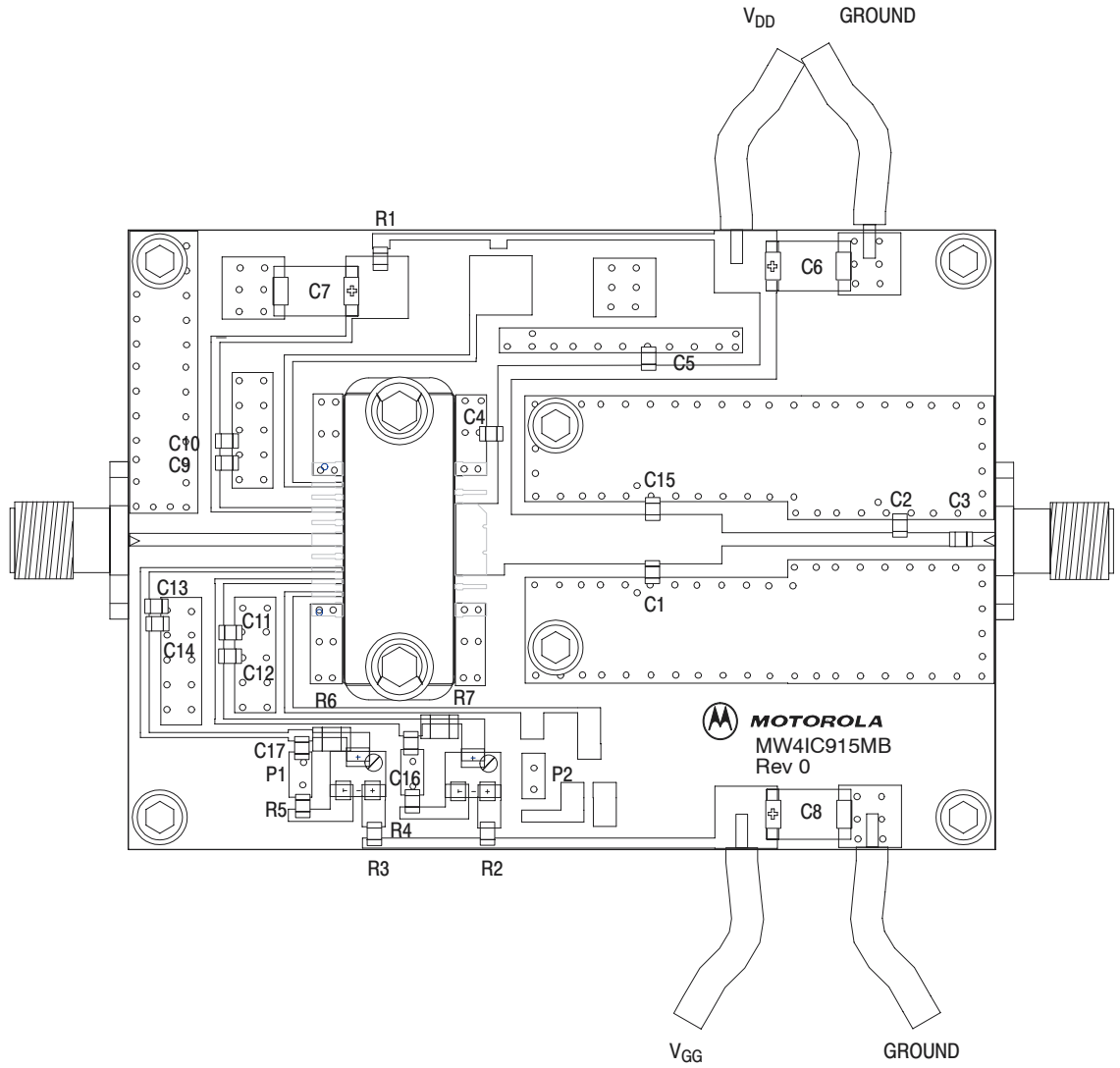


Figure 4. 860-960 MHz Reference Board Component Layout

# Freescale Semiconductor, Inc.

## TYPICAL CHARACTERISTICS (MOTOROLA TEST FIXTURE, 50 OHM SYSTEM)

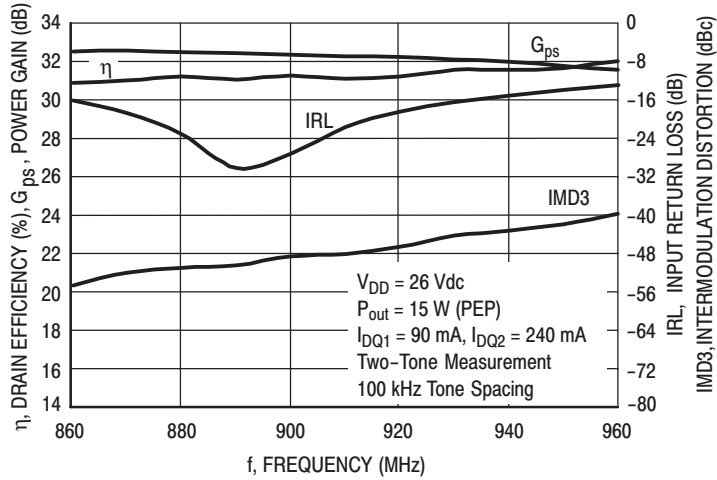


Figure 5. Two-Tone Wideband Circuit Performance

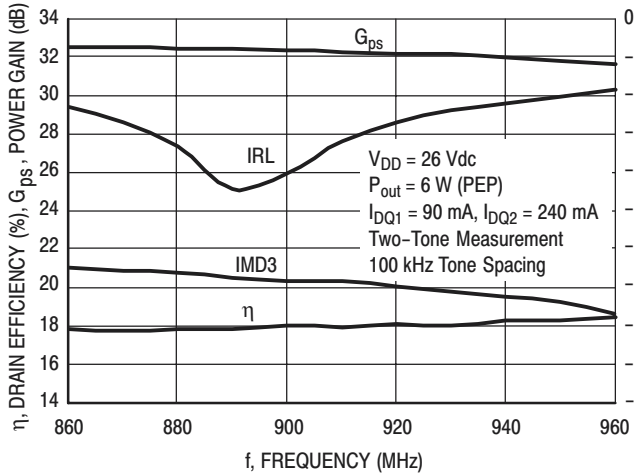


Figure 6. Two-Tone Wideband Circuit Performance

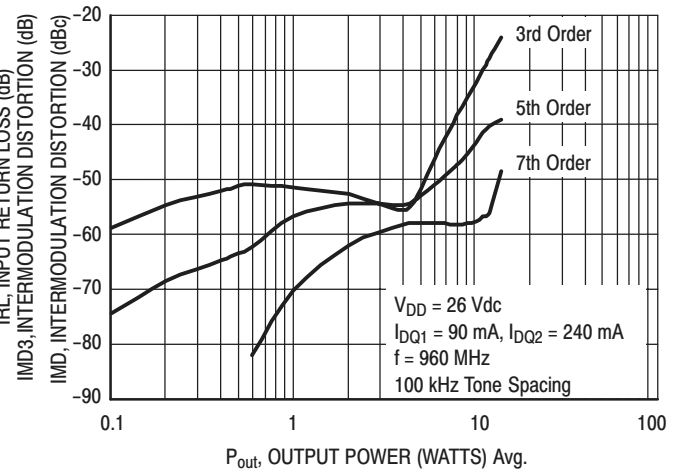


Figure 7. Intermodulation Distortion Products versus Output Power

## TYPICAL CHARACTERISTICS (MOTOROLA REFERENCE BOARD)

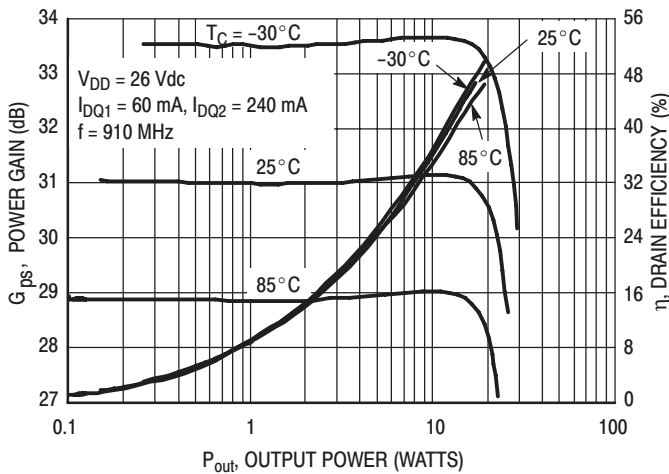


Figure 8. Power Gain and Efficiency versus Output Power

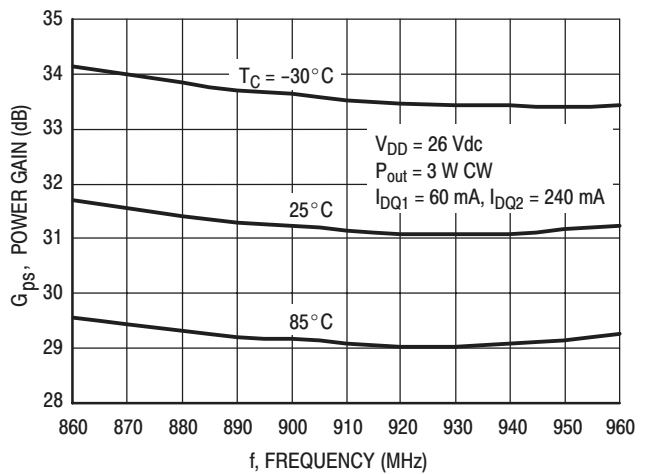


Figure 9. Power Gain versus Frequency



# Freescale Semiconductor, Inc.

## TYPICAL CHARACTERISTICS (MOTOROLA REFERENCE BOARD) - CONTINUED

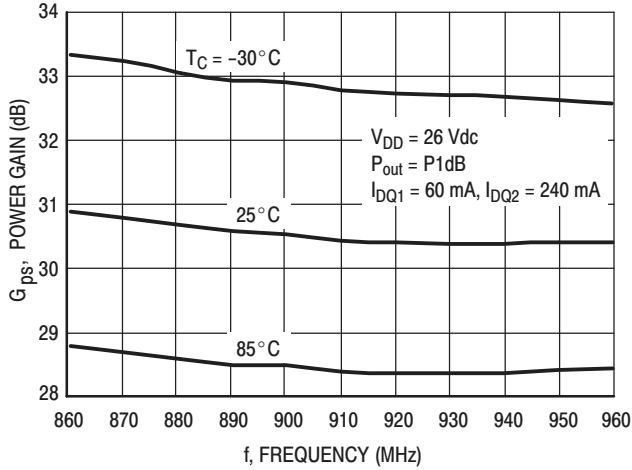


Figure 10. Power Gain versus Frequency

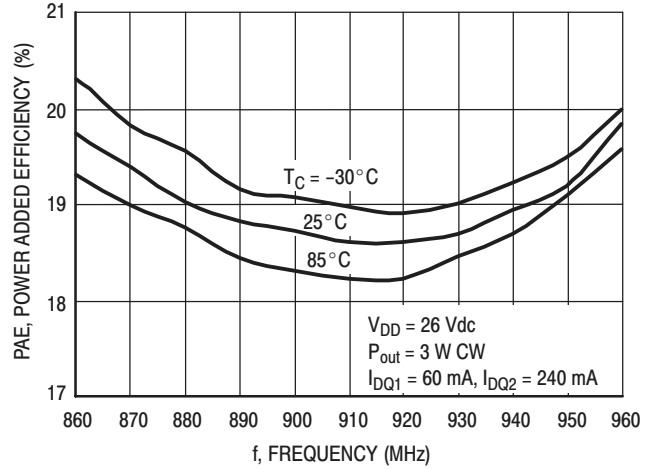


Figure 11. Power Added Efficiency versus Frequency

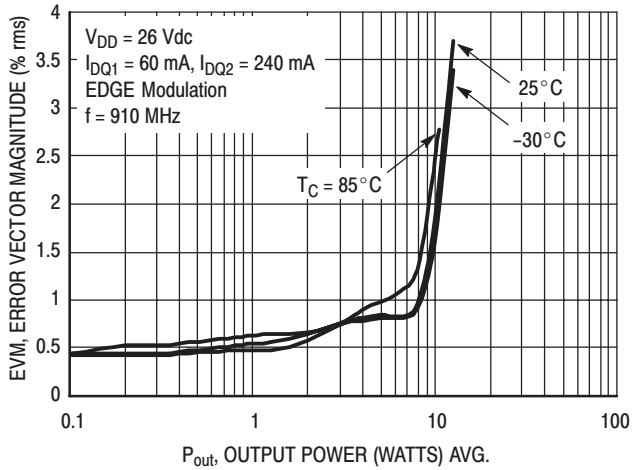


Figure 12. Error Vector Magnitude versus Output Power

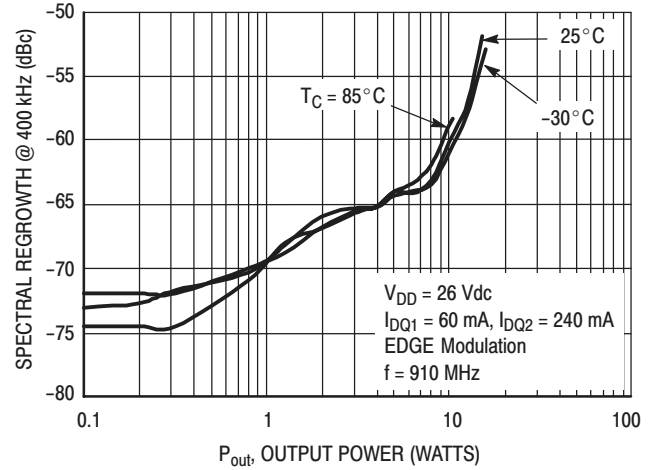


Figure 13. Spectral Regrowth at 400 kHz versus Output Power

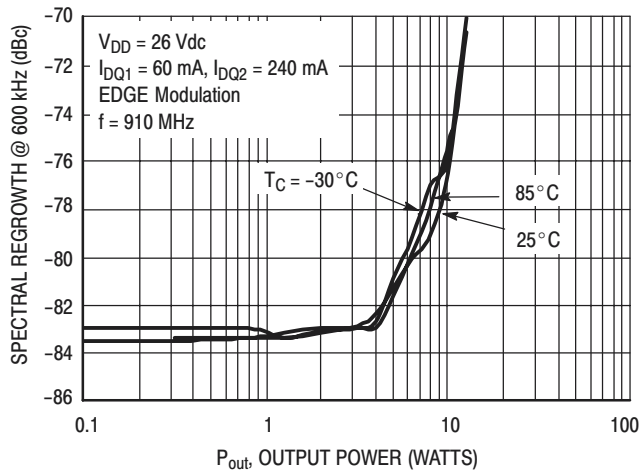
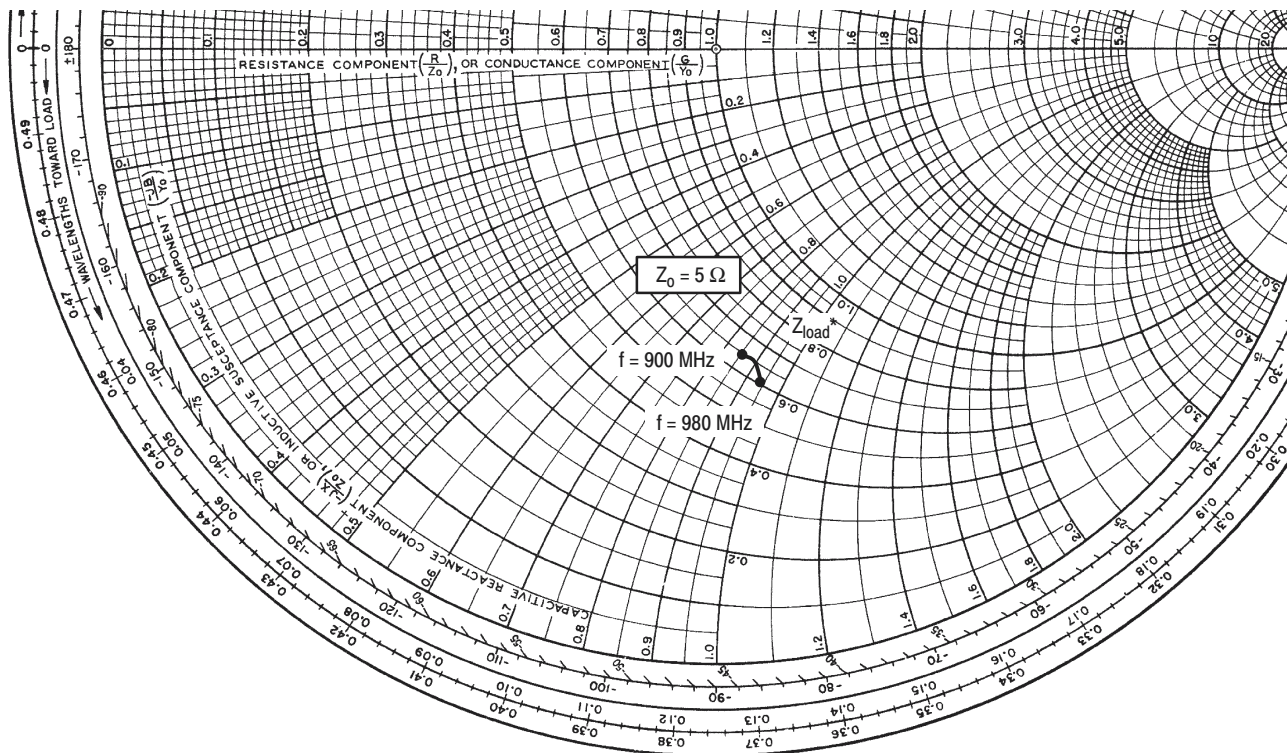


Figure 14. Spectral Regrowth at 600 kHz versus Output Power

# Freescale Semiconductor, Inc.



$V_{DD} = 26\text{ V}$ ,  $I_{DQ1} = 60\text{ mA}$ ,  $I_{DQ2} = 240\text{ mA}$ ,  $P_{out} = P_{1dB}$

f MHz	$Z_{load}$ Ω
900	3.23 - j4.30
910	3.24 - j4.36
920	3.25 - j4.42
930	3.25 - j4.47
940	3.23 - j4.52
950	3.21 - j4.56
960	3.16 - j4.60
970	3.11 - j4.65
980	3.04 - j4.70

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

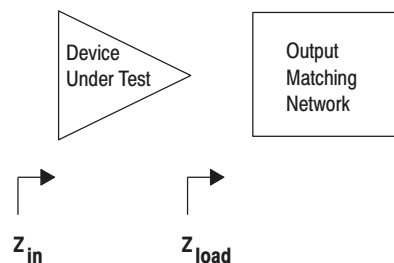


Figure 15. Series Equivalent Output Impedance

**Freescale Semiconductor, Inc.**  
**NOTES**

**Freescale Semiconductor, Inc.**

**Freescale Semiconductor, Inc.**  
**NOTES**

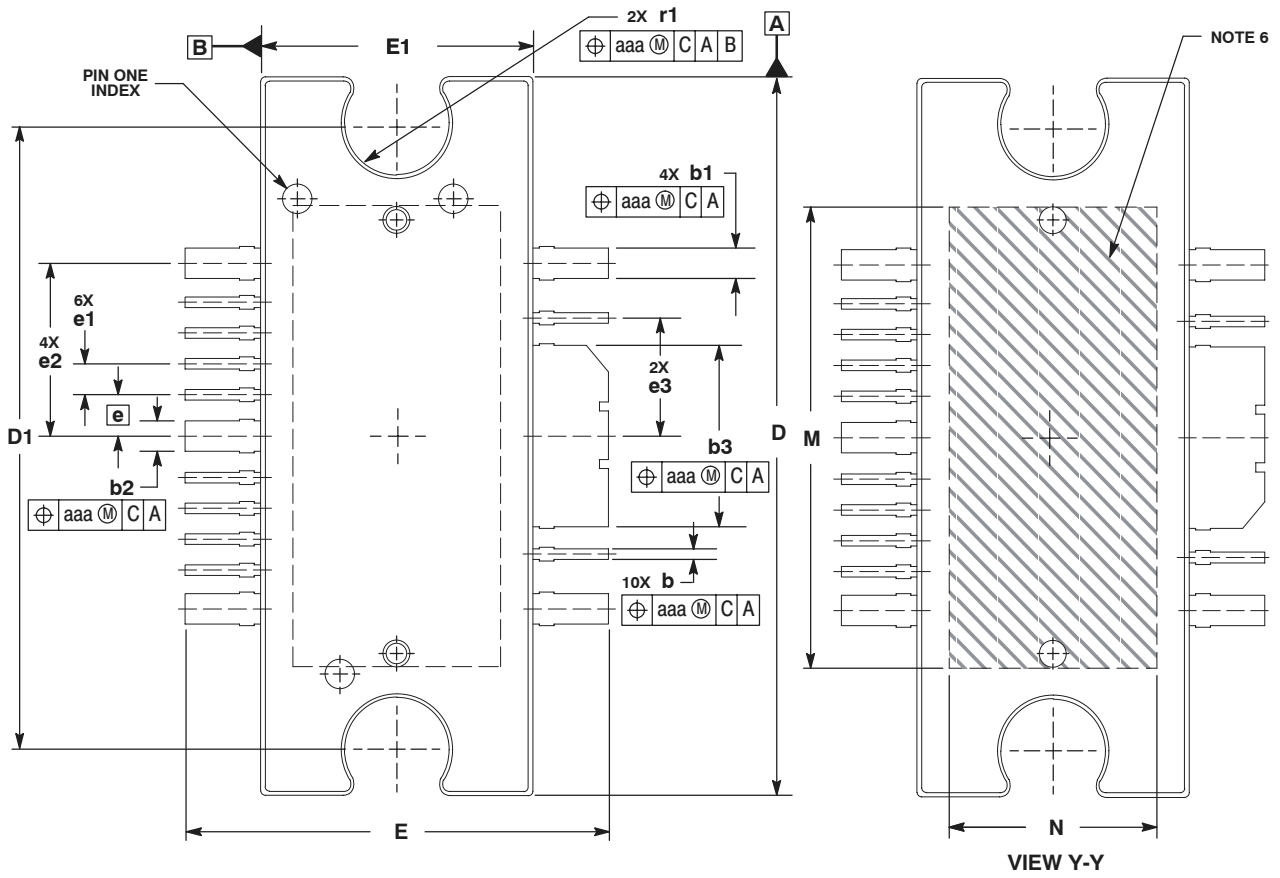
**Freescale Semiconductor, Inc.**

**Freescale Semiconductor, Inc.**  
**NOTES**

**Freescale Semiconductor, Inc.**

# Freescale Semiconductor, Inc.

## PACKAGE DIMENSIONS

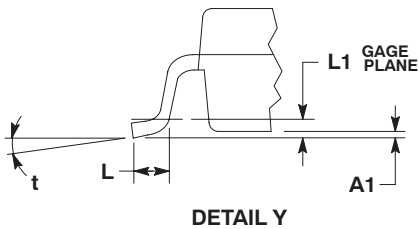
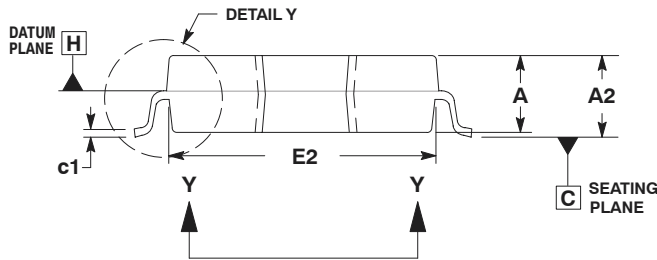
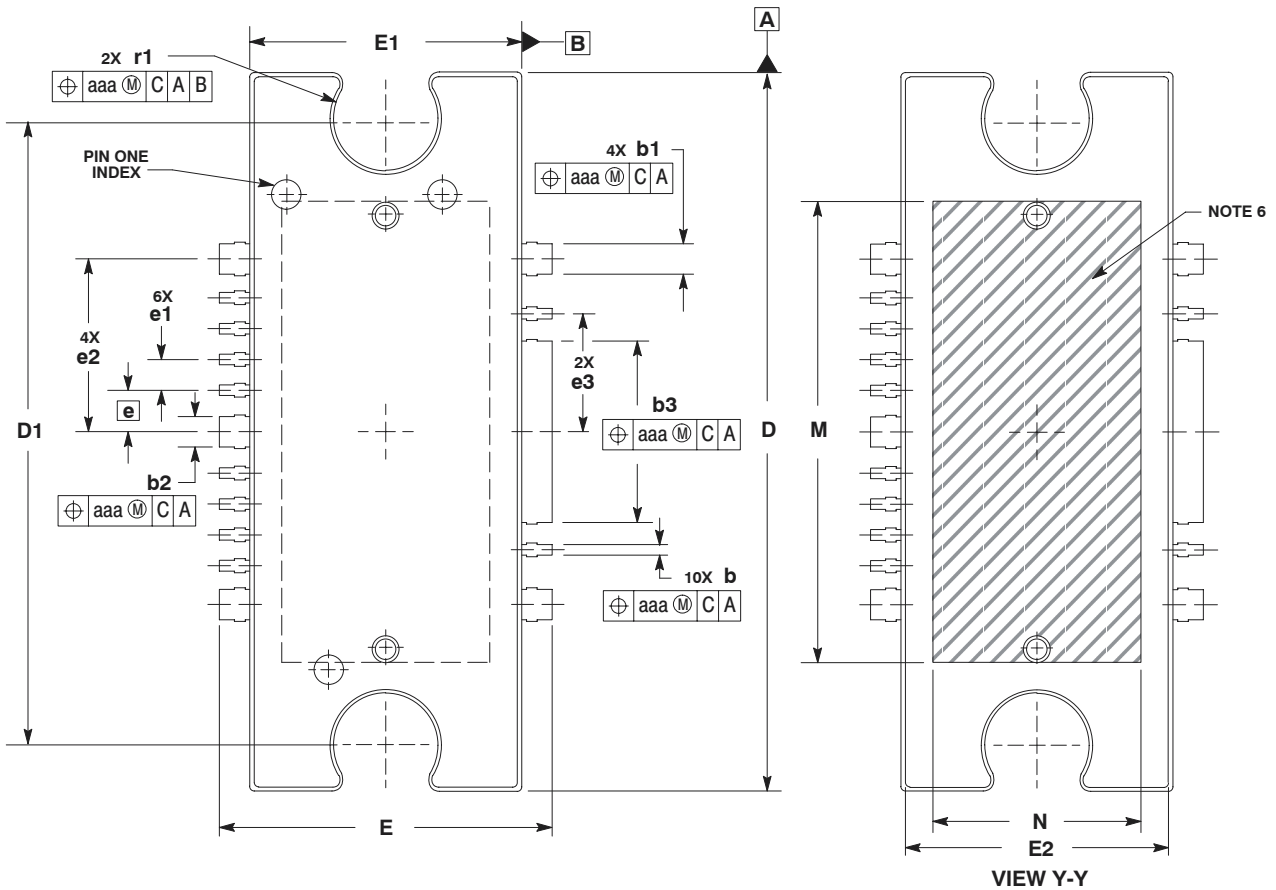


- NOTES:
1. CONTROLLING DIMENSION: INCH.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
  3. DATUM PLANE -H- IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
  4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 (0.15) PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
  5. DIMENSIONS "b", "b1", "b2" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 (0.13) TOTAL IN EXCESS OF THE "b", "b1", "b2" AND "b3" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
  6. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.
  7. DIM A2 APPLIES WITHIN ZONE "J" ONLY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.038	.044	0.96	1.12
A2	.040	.042	1.02	1.07
D	.928	.932	23.57	23.67
D1	.810 BSC		20.57 BSC	
E	.551	.559	14.00	14.20
E1	.353	.357	8.97	9.07
E2	.346	.350	8.79	8.89
F	.025 BSC		0.64 BSC	
M	.600	---	15.24	---
N	.270	---	6.86	---
b	.011	.017	0.28	0.43
b1	.037	.043	0.94	1.09
b2	.037	.043	0.94	1.09
b3	.225	.231	5.72	5.87
c1	.007	.011	.18	.28
e	.054 BSC		1.37 BSC	
e1	.040 BSC		1.02 BSC	
e2	.224 BSC		5.69 BSC	
e3	.150 BSC		3.81 BSC	
r1	.063	.068	1.6	1.73
aaa	.004		.10	

**CASE 1329-09  
ISSUE J  
TO-272 WB-16  
PLASTIC  
MW4IC915MBR1**

# Freescale Semiconductor, Inc.



- NOTES:
1. CONTROLLING DIMENSION: INCH.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
  3. DATUM PLANE -H- IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
  4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 (0.15) PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
  5. DIMENSIONS "b", "b1", "b2" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 (0.13) TOTAL IN EXCESS OF THE "b", "b1", "b2" AND "b3" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
  6. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SINK.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64
A1	.001	.004	0.02	0.10
A2	.099	.110	2.51	2.79
D	.928	.932	23.57	23.67
D1	.810 BSC		20.57 BSC	
E	.429	.437	10.90	11.10
E1	.353	.357	8.97	9.07
E2	.346	.350	8.79	8.89
L	.018	.024	4.90	5.06
L1	.01 BSC		0.25 BSC	
M	.600	---	15.24	---
N	.270	---	6.86	---
b	.011	.017	0.28	0.43
b1	.037	.043	0.94	1.09
b2	.037	.043	0.94	1.09
b3	.225	.231	5.72	5.87
c1	.007	.011	.18	.28
e	.054 BSC		1.37 BSC	
e1	.040 BSC		1.02 BSC	
e2	.224 BSC		5.69 BSC	
e3	.150 BSC		3.81 BSC	
r1	.063	.068	1.6	1.73
t	2°	8°	2°	8°
aaa	.004		.10	

**CASE 1329A-03  
ISSUE B  
TO-272 WB-16 GULL  
PLASTIC  
MW4IC915GMBR1**

# Freescale Semiconductor, Inc.

Information in this document is provided solely to enable system and software implementers to use Motorola products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals", must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part.

MOTOROLA and the Stylized M Logo are registered in the US Patent and Trademark Office. All other product or service names are the property of their respective owners. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

© Motorola Inc. 2003

#### HOW TO REACH US:

#### USA/EUROPE/LOCATIONS NOT LISTED:

Motorola Literature Distribution  
P.O. Box 5405, Denver, Colorado 80217  
1-800-521-6274 or 480-768-2130

**JAPAN:** Motorola Japan Ltd.; SPS, Technical Information Center,  
3-20-1, Minami-Azabu, Minato-ku, Tokyo 106-8573, Japan  
81-3-3440-3569

**ASIA/PACIFIC:** Motorola Semiconductors H.K. Ltd.; Silicon Harbour Centre,  
2 Dai King Street, Tai Po Industrial Estate, Tai Po, N.T., Hong Kong  
852-26668334

**HOME PAGE:** <http://motorola.com/semiconductors>